

# TSM60N03 30V N-Channel Power MOSFET



TO-252 (DPAK)



#### Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
30	4.5 @ V <sub>GS</sub> =10V	60

## **Features**

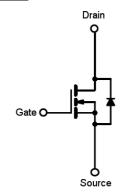
- Advanced Trench Technology
- Low  $R_{DS(ON)} 4.5 m\Omega$  (Max.)
- Low gate charge typical @ 12nC (Typ.)
- Low Crss typical @ 140pF (Typ.)

#### **Ordering Information**

Part No.	Package	Packing
TSM60N03CP ROG	TO-252	2.5Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product

## **Block Diagram**



N-Channel MOSFET

## **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	30	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Orain-Source Voltage  Gate-Source Voltage  Continuous Drain Current  Orain Current-Pulsed Note 1  Avalanche Current, L=0.1mH  Avalanche Energy, L=0.1mH  Maximum Power Dissipation	T <sub>C</sub> =25℃		60		
Continuous Drain Current	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	48	A		
Continuous Drain Current		19			
	T <sub>A</sub> =70℃				
Drain Current-Pulsed Note 1		I <sub>DM</sub>	140	Α	
Avalanche Current, L=0.1mH		I <sub>AS</sub> , I <sub>AR</sub>	38	Α	
Avalanche Energy, L=0.1mH		E <sub>AS</sub> , E <sub>AR</sub>	72	mJ	
	T <sub>C</sub> =25℃		41		
Mayimum Dayyar Disaination	T <sub>C</sub> =70℃	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	1		
Maximum Power Dissipation	T <sub>A</sub> =25℃	$P_{D}$	2.5	W	
	T <sub>A</sub> =70℃		1.6		
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	$\mathcal{L}$	
Operating Junction Temperature Range		TJ	-55 to +150	C	

<sup>\*</sup> Limited by maximum junction temperature

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R⊖ <sub>JC</sub>	3	°C/W
Thermal Resistance - Junction to Ambient	R⊖ <sub>JA</sub>	50	°C/W

Notes: Surface mounted on FR4 board t ≤ 10sec



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**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	100			V
Proin Course On State Besistance	$V_{GS} = 10V, I_D = 19A$	R <sub>DS(ON)</sub>		3.5	4.5	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 16A$	R <sub>DS(ON)</sub>		4.6	5.8	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	1.15		2.2	V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I <sub>DSS</sub>			1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Dynamic						
Total Gate Charge	\/ 00\/ I 40A	$Q_g$		12		
Gate-Source Charge	$V_{DS} = 30V, I_{D} = 19A,$	$Q_{gs}$		5.4		nC
Gate-Drain Charge	V <sub>GS</sub> = 4.5V	$Q_{gd}$		4.6		
Input Capacitance	N 00V N 0V	C <sub>iss</sub>		1700		
Output Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		350		pF
Reverse Transfer Capacitance	I = I.UIVIMZ	$C_{rss}$		140		
Switching						
Turn-On Delay Time		t <sub>d(on)</sub>		25		
Turn-On Rise Time	$V_{GS} = 4.5V, V_{DS} = 30V,$	t <sub>r</sub>		20		0
Turn-Off Delay Time	$R_G = 1.5\Omega$	$t_{d(off)}$		25		nS
Turn-Off Fall Time		t <sub>f</sub>		15		
<b>Drain-Source Diode Characteristic</b>	s and Maximum Rating					
Drain-Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =10A	V <sub>SD</sub>	-	0.8	1.2	V
Reverse Recovery Time	I <sub>S</sub> = 10A, T <sub>J</sub> =25 °C	t <sub>fr</sub>		25		nS
Reverse Recovery Charge	dI/dt = 100A/us	Q <sub>fr</sub>		17		nC

#### Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2.  $R\theta_{JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R\theta_{JC}$  is guaranteed by design while  $R\theta_{CA}$  is determined by the user's board design.  $R\theta_{JA}$  shown below for single device operation on FR-4 in still air

3. The maximum current rating is limited by package

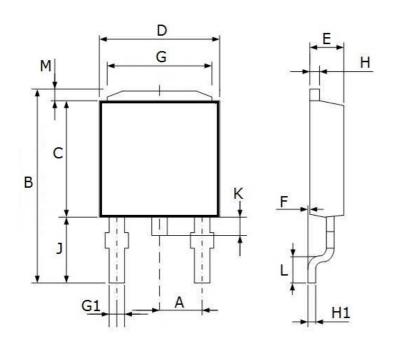


## **TSM60N03**

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## **TO-252 Mechanical Drawing**



TO-252 DIMENSION						
DIM	MILLIM	ETERS	INCHES			
ווועו	MIN	MAX	MIN	MAX		
Α	2.286	BSC	0.090 BSC			
В	9.40	10.40	0.370	0.409		
С	5.40	6.23	0.213	0.245		
D	6.40	6.80	0.252	0.268		
Е	2.20	2.40	0.087	0.094		
F	0.00	0.20	0.000	0.008		
G	5.20	5.50	0.205	0.217		
G1	0.50	0.91	0.020	0.036		
Н	0.45	0.60	0.018	0.024		
H1	0.40	0.60	0.016	0.024		
J	2.50	2.90	0.098	0.114		
K	0.60	1.00	0.023	0.039		
L	1.40	1.78	0.055	0.070		
М	0.88	1.28	0.034	0.050		



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